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April 2014



FQA19N60

N-Channel QFET® MOSFET

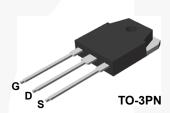
600 V, 18.5 A, $380 \text{ m}\Omega$

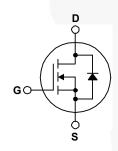
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 18.5 A, 600 V, R_{DS(on)} = 380 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.3 A
- Low Gate Charge (Typ. 70 nC)
- · Low Crss (Typ. 35 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA19N60	Unit	
V _{DSS}	Drain-Source Voltage		600	V	
I _D	Drain Current - Continuous (T _C = 25°	C)	18.5	А	
	- Continuous (T _C = 100°C)		11.7	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	74	Α	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	Pulsed Avalanche Energy (Note 2) 1150		mJ	
I _{AR}	Avalanche Current	(Note 1)	18.5	Α	
E _{AR}	Repetitive Avalanche Energy (Note		30	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns	
P_{D}	Power Dissipation (T _C = 25°C)		300	W	
	- Derate above 25°C		2.38	W/°C	
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering,		300	°C	
· L	1/8" from Case for 5 Seconds		330		

Thermal Characteristics

Symbol	Parameter	FQA19N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA19N60	FQA19N60	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_c = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to 25°C		0.65		V/°C
I _{DSS} Zero Gate Voltage Drain Current	Zara Cata Valtaga Prain Current	V _{DS} = 600 V, V _{GS} = 0 V			10	μΑ
	V _{DS} = 480 V, T _C = 125°C			100	μΑ	
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10 V, I _D =9.3 A		0.3	0.38	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_{D} = 9.3 \text{ A}$		16		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		2800	3600	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		350	450	pF
C _{rss}	Reverse Transfer Capacitance			35	45	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 18.5 A,		65	140	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		210	430	ns
t _{d(off)}	Turn-Off Delay Time	NG = 25 12		150	310	ns
t _f	Turn-Off Fall Time	(Note 4)		135	280	ns
Qg	Total Gate Charge	V _{DS} = 480 V, I _D = 18.5 A,	/	70	90	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		17		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	<i>y</i>	33		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				18.5	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				74	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 18.5 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 18.5 A,		420		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		4.7		μС

- Notes: Notes: 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 6.2 mH, I_{AS} = 18.5 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} ≤ 18.5 A, di/dt ≤ 200 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

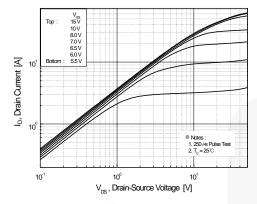


Figure 1. On-Region Characteristics

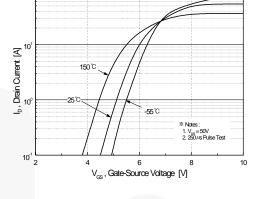


Figure 2. Transfer Characteristics

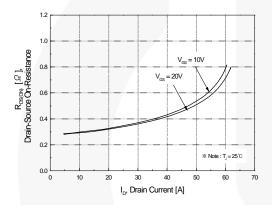


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

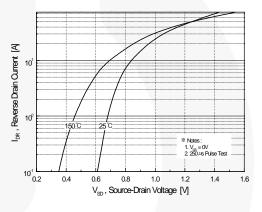


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

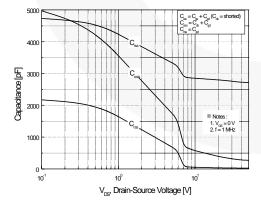


Figure 5. Capacitance Characteristics

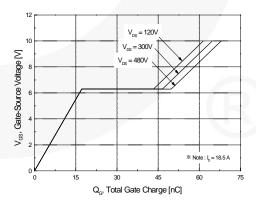


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

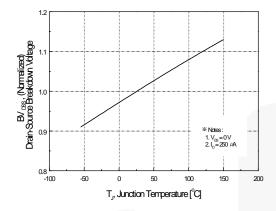


Figure 7. Breakdown Voltage Variation vs. Temperature

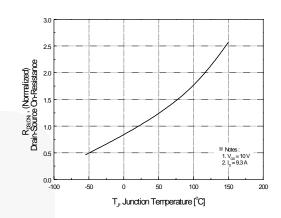


Figure 8. On-Resistance Variation vs. Temperature

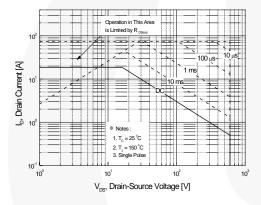


Figure 9. Maximum Safe Operating Area

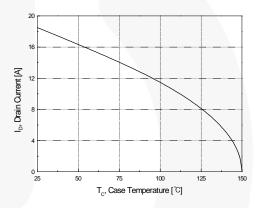


Figure 10. Maximum Drain Current vs. Case Temperature

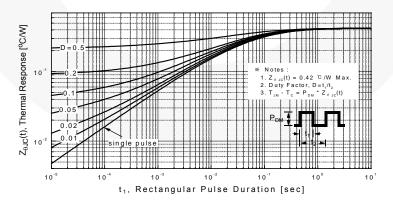


Figure 11. Transient Thermal Response Curve

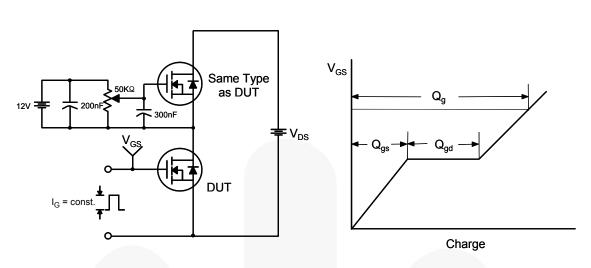


Figure 12. Gate Charge Test Circuit & Waveform

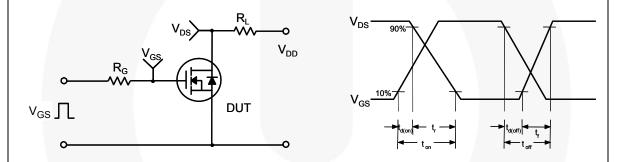


Figure 13. Resistive Switching Test Circuit & Waveforms

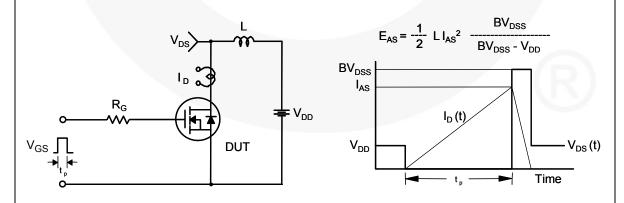
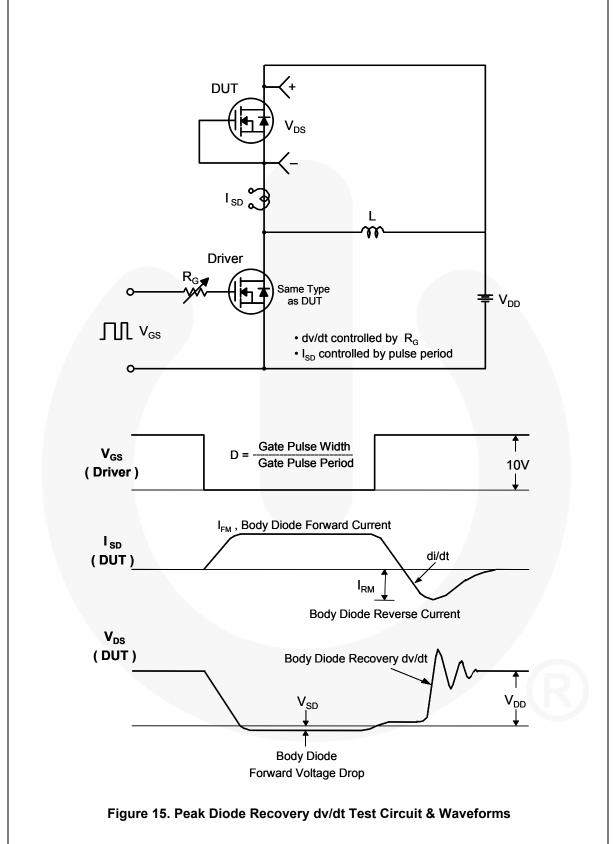


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

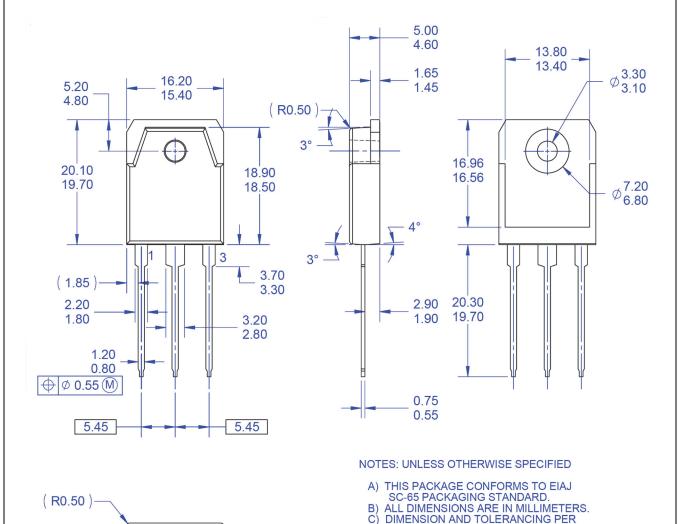


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

ASME14.5-2009.

D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
E) DRAWING FILE NAME: TO3PN03AREV1.

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